

BCW33

NPN General Purpose Amplifier

- This device is designed for general purpose applications at collector currents to 300mA.
- Sourced from process 07.



1. Base 2. Emitter 3. Collector

Absolute Maximum Ratings * T_a=25°C unless otherwise noted

Symbol	Parameter	Value	Units	
V _{CEO}	Collector-Emitter Voltage	32	V	
V _{CBO}	Collector-Base Voltage	32	V	
V _{EBO}	Emitter-Base Voltage	5.0	V	
I _C	Collector current (DC)	500	mA	
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 ~ +150	°C	

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

- NOTES:

 1) These ratings are based on a maximum junction temperature of 150 degrees C.

 2) These are state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Electrical Characteristics T_a=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
Off Charact	Off Characteristics					
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_C = 2.0 \text{mA}, I_B = 0$	32			V
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	$I_{C} = 10\mu A, I_{B} = 0$	32			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_C = 10\mu A, I_C = 0$	5.0			V
ІСВО	Collector Cutoff Current	$V_{CB} = 32V, I_{E} = 0$ $V_{CB} = 32V, I_{E} = 0, T_{A} = 100^{\circ}C$			100 10	nA μA
On Charact	On Characteristics					•
h _{FE}	DC Current Gain	I _C = 2.0mA, V _{CE} = 5.0V	420		800	
V _{CE(sat)}	Collector-Emitter Saturation Voltage	$I_C = 10 \text{mA}, I_B = 0.5 \text{mA}$			0.25	V
V _{BE(on)}	Base-Emitter On Voltage	I _C = 2.0mA, V _{CE} = 5.0V	0.55		0.7	V
Small Signal Characteristics						
f _T	Current Gain Bandwidth Product	$I_C = 2.0 \text{mA}, V_{CE} = 5.0 \text{V}$ f = 35MHz	200			
C _{obo}	Output Capacitance	$V_{CB} = 10V, I_E = 0, f = 1.0MHz$			4.0	pF
NF	Noise Figure	$I_C = 0.2\text{mA}, V_{CE} = 5.0\text{V}$ $R_S = 2.0\text{k}\Omega, f = 1.0\text{kHz}$ $B_W = 200\text{Hz}$			10	dB

Thermal Characteristics T_A=25°C unless otherwise noted

Symbol	Parameter	Max.	Units	
P _D	Total Device Dissipation		mW	
	Derate above 25°C	2.8	mW/°C	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient 357		°C/W	
Device mounted on FR-4PCB 40mm × 40mm × 1.5mm				

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Typical Characteristics

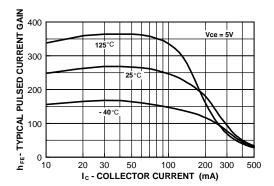


Figure 1. Typical Pulsed Current Gain vs Collector Current

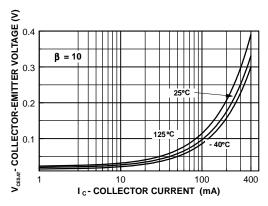


Figure 2. Collector-Emitter Saturation Voltage vs Collector Current

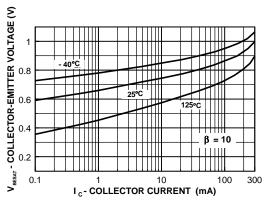


Figure 3. Base-Emitter Saturation Voltage vs Collector Current

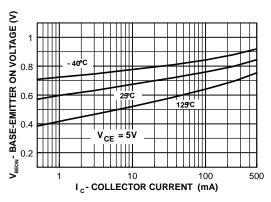


Figure 4. Base-Emitter On Voltage vs Collector Current

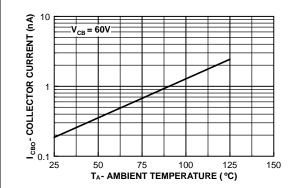


Figure 5. Collector-Cutoff Current vs Ambient Temperature

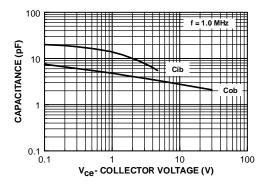


Figure 6. Input and Outtput Capacitance vs Reverse Voltage

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Typical Characteristics (Continued)

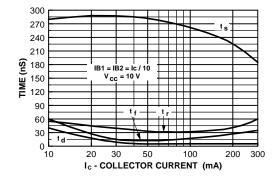


Figure 7. Switching Times vs Collector Current

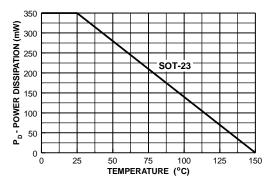
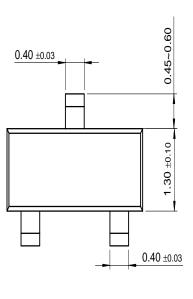


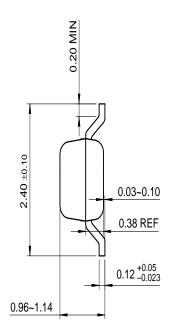
Figure 8. Power Dissipation vs Ambient Temperature

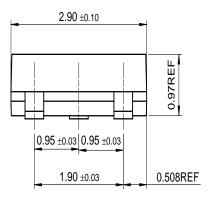
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Package Dimensions

SOT-23







Dimensions in Millimeters

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